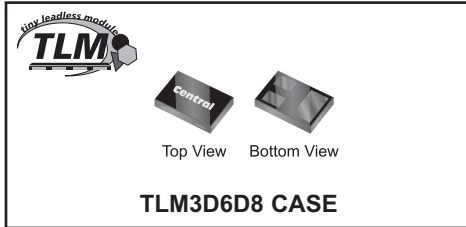


CTLDM3590**SURFACE MOUNT
N-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET**
www.centrasemi.com
**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CTLDM3590 is an enhancement-mode N-channel MOSFET designed for applications including high speed pulsed amplifiers and drivers. This MOSFET has beneficially low $r_{DS(ON)}$, low threshold voltage, and very low gate charge characteristics.

MARKING CODE: 1**FEATURES:**

- ESD protection up to 2kV
- Power dissipation: 125mW
- Low $r_{DS(ON)}$
- Low threshold voltage
- Ultra small, ultra low profile 0.6mm x 0.8mm x 0.4mm TLM™ leadless surface mount package

APPLICATIONS:

- Load/Power Switches
- Boost/Buck Converters
- Battery Charging/Power Management

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Drain-Source Voltage
Gate-Source Voltage
Continuous Drain Current (Steady State)
Pulsed Drain Current, $t_p=10\mu\text{s}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL		UNITS
V_{DS}	20	V
V_{GS}	8.0	V
I_D	160	mA
I_D	800	mA
P_D	125	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Θ_{JA}	1000	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

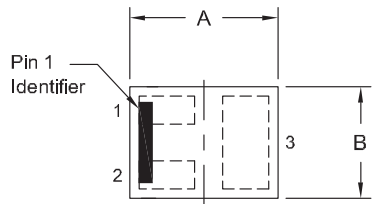
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=5.0\text{V}, V_{DS}=0$			100	nA
I_{DSS}	$V_{DS}=5.0\text{V}, V_{GS}=0$			50	nA
I_{DSS}	$V_{DS}=16\text{V}, V_{GS}=0$			100	nA
BV_{DSS}	$V_{GS}=0, I_D=250\mu\text{A}$	20			V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.4		1.0	V
$r_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=100\text{mA}$		1.5	3.0	Ω
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=50\text{mA}$		2.0	4.0	Ω
$r_{DS(ON)}$	$V_{GS}=1.8\text{V}, I_D=20\text{mA}$		3.0	6.0	Ω
$r_{DS(ON)}$	$V_{GS}=1.5\text{V}, I_D=10\text{mA}$		4.0	10	Ω
$r_{DS(ON)}$	$V_{GS}=1.2\text{V}, I_D=1.0\text{mA}$		7.0		Ω
$Q_g(\text{tot})$	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=100\text{mA}$		0.458		nC
Q_{gs}	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=100\text{mA}$		0.176		nC
Q_{gd}	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=100\text{mA}$		0.138		nC
g_{FS}	$V_{DS}=5.0\text{V}, I_D=125\text{mA}$		1.3		S
C_{rss}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		2.2		pF
C_{iss}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		9.0		pF
C_{oss}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		3.0		pF
t_{on}	$V_{DD}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}$		25		ns
t_{off}	$V_{DD}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}$		85		ns

R3 (27-September 2012)

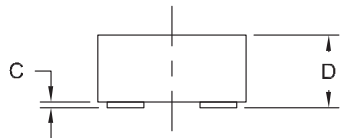
CTLDM3590
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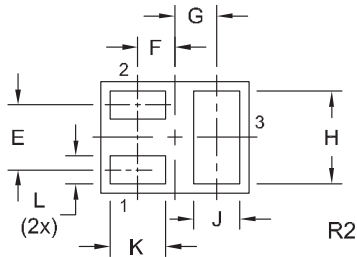
TLM3D6D8 CASE - MECHANICAL OUTLINE



TOP VIEW



SIDE VIEW

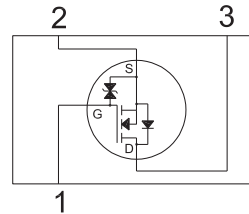


BOTTOM VIEW

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.029	0.034	0.75	0.85
B	0.021	0.026	0.55	0.65
C	0.000	0.002	0.00	0.05
D	0.012	0.016	0.31	0.40
E	0.014		0.35	
F	0.008		0.20	
G	0.009		0.225	
H	0.017	0.022	0.45	0.55
J	0.008	0.012	0.20	0.30
K	0.010	0.014	0.25	0.35
L	0.004	0.008	0.10	0.20

TLM3D6D8 (REV: R2)

PIN CONFIGURATION
(Bottom View)



LEAD CODE:

- 1) Gate
- 2) Source
- 3) Drain

MARKING CODE: 1

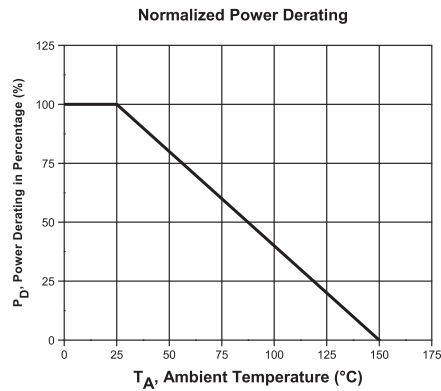
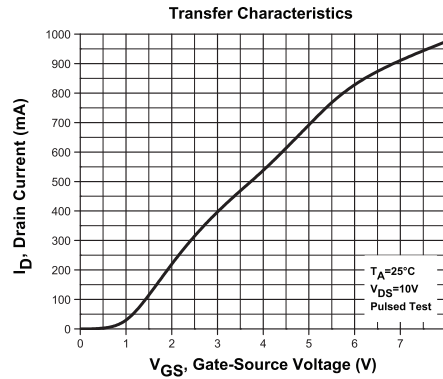
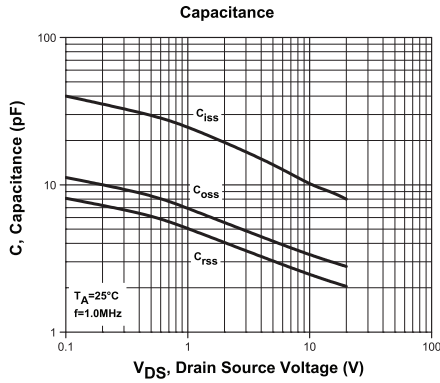
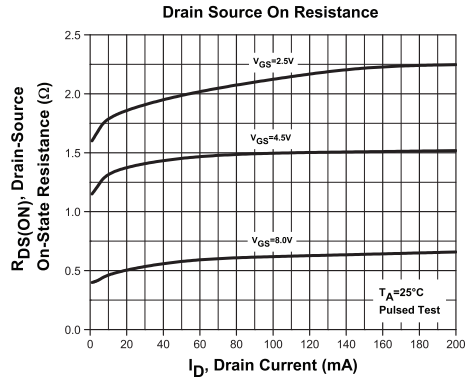
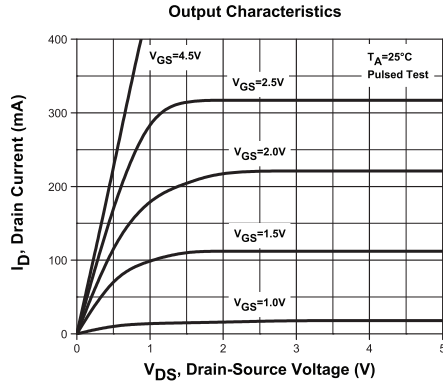
R3 (27-September 2012)

CTLDM3590

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TYPICAL ELECTRICAL CHARACTERISTICS



R3 (27-September 2012)